

TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type
Four Darlingtons Power Transistors in One)

MP4024

High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 10 pins)
- Built-in resistance (R_B).
- Surge voltage is clamped by zener diode (C-B).
- Low $V_{CE(sat)}$: $V_{CE(sat)} = 1.5 \text{ V (max)}$ ($I_C = 1 \text{ A}$, $V_{BH} = 4.2 \text{ V}$)
- High DC current gain: $h_{FE} = 2000 \text{ (min)}$ ($V_{CE} = 2 \text{ V}$, $I_C = 1 \text{ A}$)

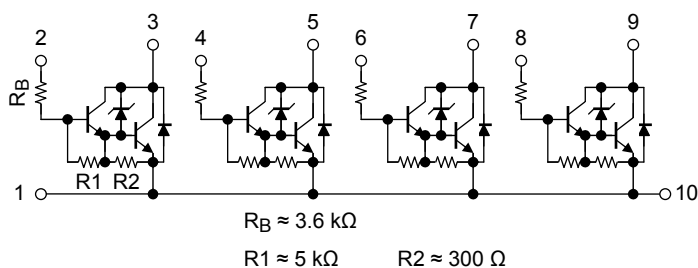
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	85	V
Collector-emitter voltage		V_{CEO}	100 ± 15	V
Emitter-base voltage		V_{EBO}	6	V
Input voltage		V_B	20	V
Collector current	DC	I_C	3	A
	Pulse	I_{CP}	4	
Collector power dissipation (1-device operation)		P_C	2.0	W
Collector power dissipation (4-device operation)		P_T	4.0	W
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

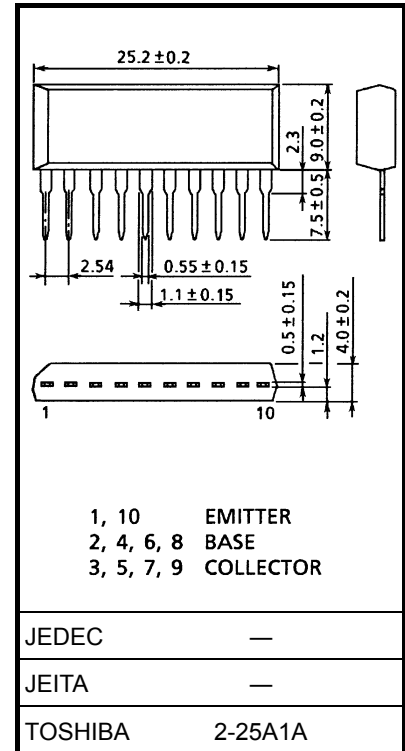
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



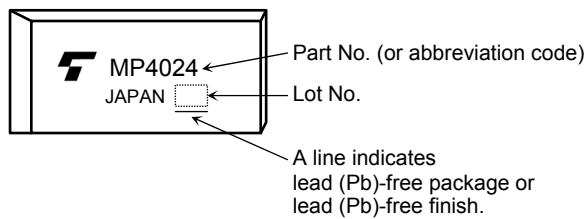
Industrial Applications

Unit: mm



Weight: 2.1 g (typ.)

Marking

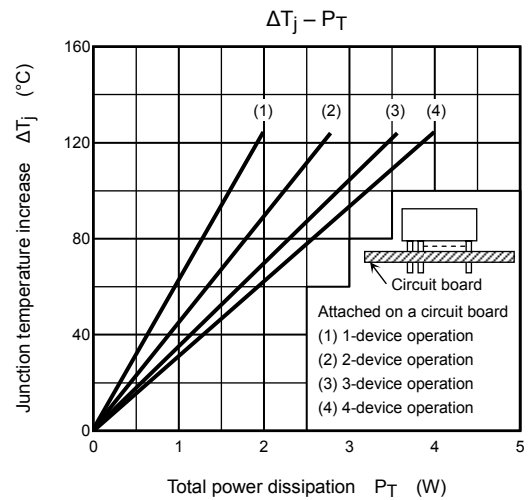
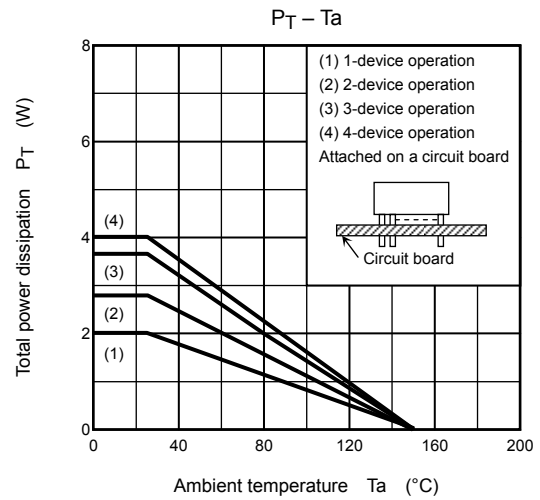
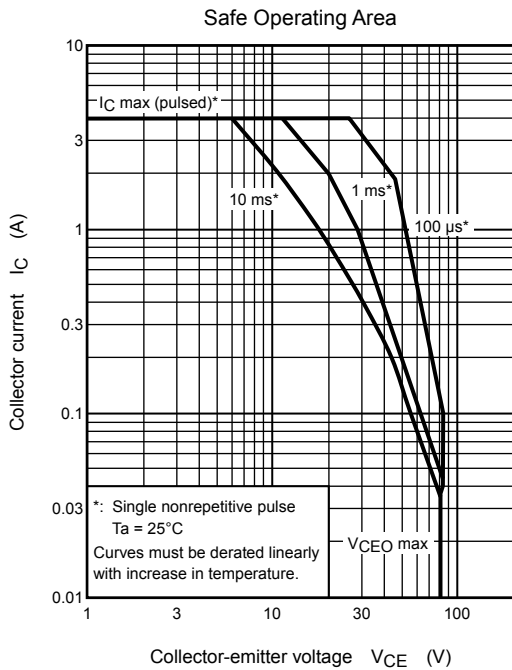
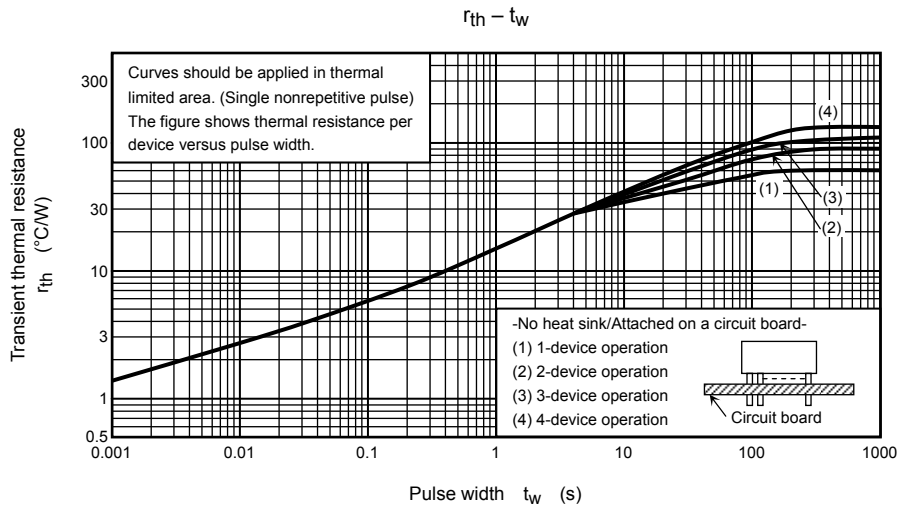


Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance from junction to ambient (4-device operation, $T_a = 25^\circ\text{C}$)	$\Sigma R_{th(j-a)}$	31.3	$^\circ\text{C/W}$
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	T_L	260	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 80\text{ V}, I_E = 0\text{ A}$	—	—	10	μA
Collector cut-off current		I_{CEO}	$V_{CE} = 80\text{ V}, I_B = 0\text{ A}$	—	—	10	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 6\text{ V}, I_C = 0\text{ A}$	0.3	—	1.5	mA
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0\text{ A}$	85	100	115	V
Resistance		R_B	—	2.5	3.6	4.7	$\text{k}\Omega$
DC current gain		$h_{FE(1)}$	$V_{CE} = 2\text{ V}, I_C = 1\text{ A}$	2000	—	—	—
		$h_{FE(2)}$	$V_{CE} = 2\text{ V}, I_C = 2\text{ A}$	1000	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)(1)}$	$I_C = 1\text{ A}, V_{BH} = 4.2\text{ V}$	—	—	1.5	V
		$V_{CE(sat)(2)}$	$I_C = 1.5\text{ A}, V_{BH} = 9\text{ V}$	—	—	1.5	
Input voltage (low)		V_{BL}	$V_{CE} = 50\text{ V}, I_C = 100\text{ }\mu\text{A}$	—	—	0.7	V
Switching time	Turn-on time	t_{on}	<p>Duty cycle $\leq 1\%$</p>	—	0.3	—	μs
	Storage time	t_{stg}		—	4.0	—	
	Fall time	t_f		—	0.6	—	



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